Slotted Optical Flag Switch

OPB850A, OPB850-1Z

Electronics



Features:

- Snap into PCBoard mounting
- Transistor output
- Mechanical switch replacement
- Four 18" (457 mm) 26 AWG, UL wires for electrical connections
- Choice of phototransistor or Rbe phototransistor output

Description:

Each **OPB850A** switch has a NPN phototransistor coupled with a 940 nm gallium arsenide infrared emitting diode in a molded plastic housing. Each **OPB850-1Z** has a Rbe phototransistor coupled with an 880 nm gallium arsenide infrared emitting diode in a molded plastic housing. An actuated lever arm flag interrupts the light beam, which switches the transistor output between states that can readily drive logic gates.

These devices are designed to replace conventional mechanical limit switches where long life and reliability are critical. The switches are designed to easily snap mount into a 0.036 inch (0.914 mm) 20 gage thick material with a rectangular opening of 0.315" x 0.472 " $(8.0 \text{ mm} \times 12.0 \text{ mm})$.

Minor differences exist in the package between the **OPB850A** and **OPB850-1Z** (see drawings below). The cable exits the package in different locations.

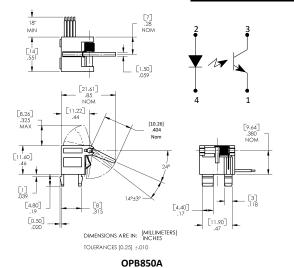
Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

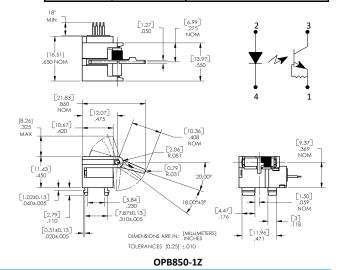
Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

| ОРВ850А, | OPB850-1Z |
|---------------|-------------|
| Pin # / Color | Description |
| 1-Black | Emitter |
| 2-Red | Anode |
| 3-Brown | Collector |
| 4-Orange | Cathode |

| Ordering Information | | | | | | |
|----------------------|------------|---|--|--|--|--|
| Part Number | Wavelength | Description | | | | |
| OPB850A | 940 nm | Slotted Optical Flag Switch 18" (457 mm) wires | | | | |
| OPB850-1Z | 880 nm | Slotted Optical Flag Switch 18" (457 mm) wires | | | | |





General Note

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TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25 °C unless otherwise noted)

| Operating Temperature Range | -20 °C to +75 °C |
|--|------------------|
| Storage Temperature Range | -40 °C to +85 °C |
| Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron] | 260 °C |
| Input Diode | |
| Reverse Voltage | 5 V |
| Continuous Forward Current | 50 mA |
| Peak Forward Current (10 μs pulse width, 300 pps) | 1 A |
| Power Dissipation | 75 mW |
| Output Phototransistor | |
| Collector-Emitter Voltage | 24 V |
| Emitter-Collector Voltage | 5 V |
| Collector DC Current | 20 mA |
| Power Dissipation | 100 mW |

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OPB850A, OPB850-1Z



Electrical Specifications

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|----------------------|--|-----|-----|------|-------|---|
| Input Dio | de | | | | | |
| V_{F} | Forward Voltage | - | 1.2 | 1.6 | V | I _F = 20 mA |
| I _R | Reverse Current | - | - | - | μΑ | V _R = 2 V |
| Output Ph | nototransistor (OPB850A) | 1 | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | 30 | - | - | V | I _C = 100 μA, E _E = 0 |
| V _{(BR)ECO} | Emitter-Collector Breakdown Voltage | 5 | - | - | V | I _E = 100 μA, E _E = 0 |
| I _{CEO} | Collector-Emitter Dark Current | - | - | 100 | nA | V _{CE} = 10 V, E _E = 0 |
| Coupled (| (OPB850A) | | | | | |
| V _{CE(SAT)} | Collector-Emitter Saturation Voltage (1) | - | - | 0.4 | V | I _C = 250 μA, I _F = 20 mA |
| I _{C(ON)} | On-State Collector Current (1) | 0.5 | 2 | - | mA | V _{CE} = 5 V, I _F = 20 mA |
| I _{C(OFF)} | Off-State Collector Current (2) | - | - | 10 | μΑ | V _{CE} = 5 V, I _F = 20 mA |
| Output Ph | nototransistor (OPB850-1Z) | | | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | 24 | 1 | - | ٧ | $I_C = 100 \mu A, E_E = 0$ |
| $V_{(BR)ECO}$ | Emitter-Collector Breakdown Voltage | 0.4 | - | - | ٧ | I _E = 100 μA, E _E = 0 |
| I _{CEO} | Collector-Emitter Dark Current | - | - | 100 | nA | V _{CE} = 10 V, E _E = 0 |
| Coupled (| (OPB850-1Z) | | | | | |
| V _{CE(SAT)} | Collector-Emitter Saturation Voltage (1) | - | - | 0.40 | V | I _C = 500 μA, I _F = 20 mA |
| I _{C(ON)} | On-State Collector Current (1) | 0.5 | 2 | - | mA | V _{CE} = 10 V, I _F = 20 mA |
| I _{C(OFF)} | Off-State Collector Current (2) | - | - | 10 | μΑ | V _{CE} = 10 V, I _F = 20 mA |

Notes:

- (1) ON (I_{C(ON)}) electrical condition corresponds to the switch point at about 41° angular displacement of the arm.
- (2) OFF (I_{C(OFF)}) electrical condition corresponds to the mechanical arm position at rest.
- (3) From the rest position to the switch point, lever torque measured at the end of the arm is 1.5 grams maximum.
- (4) Wires are 26 AWG, UL rated.

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